1. (amended) A method of forming a doped A site deficient **[thin film]** manganate material on a substrate from corresponding precursor(s), comprising liquid delivery and flash vaporization thereof to yield a precursor vapor, and transporting the precursor vapor to a chemical vapor deposition reactor for chemical vapor deposition formation of the **[thin film]** manganate material on the substrate**, said manganate material having a formula of $La_xM_yMnO_3$, where M = Mg, Ca, Sr, or Ba, and $0.5 < (x+y) < 0.9$.**

2. (amended) **[A] The** method according to claim 1, wherein the precursor(s) comprise coordination compounds, or Lewis base complexes of **[the same, of]** metal(s) selected from the group consisting of lanthanum, magnesium, calcium, strontium, barium, and manganese.

3. (amended) **[A] The** method according to claim 1, wherein the precursor(s) include metal ß-diketonate compounds, metal pivalate compounds, or Lewis base complexes thereof.

4. (amended) **[A] The** method according to claim 1, wherein the precursor(s) include metal fluorinated ß-diketonate compounds, or Lewis base complexes thereof.

5. (amended) **[A] The** method according to claim 1, wherein the precursor(s) include metal pivalate Lewis base adducts.

6. (amended) **[A] The** method according to claim 1, wherein the **[thin film]** manganate material is selected from the group consisting of **[LaMgMnO, LaCaMnO, LaSrMno, and LaBaMnO]** **$La_xMg_yMnO_3$, $La_xCa_yMnO_3$, $La_xSr_yMnO_3$, $La_xBa_yMnO_3$, wherein $0.5 < (x+y) < 0.9$.**

7. (amended) **[A]** **The** method according to claim 1, wherein the precursor(s) are dissolved in a solvent and flash vaporized at a temperature of from about 100 °C to about 300 °C.

8. (amended) **[A]** **The** method according to claim 1, wherein the precursor vapor is transported to the chemical vapor deposition reactor in a carrier gas.

9. (amended) **[A]** **The** method according to claim 8, wherein the carrier gas is selected from the group consisting of argon, nitrogen, neon, helium and ammonia.

10. (amended) **[A]** **The** method according to claim 8, wherein the carrier gas is mixed with an oxidizing co-reactant gas in the chemical vapor deposition reactor or prior to transport to the chemical vapor deposition reactor.

11. (amended) **[A]** **The** method according to claim 1, wherein the chemical vapor deposition reactor contains a substrate article heated to a temperature in the range of from about 300 °C to about 1000 °C.

12. (amended) **[A]** **The** method according to claim 11, wherein the pressure of the precursor vapor in the chemical vapor deposition reactor is from about 0.1 to about 760 Torr.

13. (amended) **[A]** **The** method according to claim 1, wherein the chemical vapor deposition is plasma-assisted.

14. (amended) **[A]** **The** method according to claim 1, wherein the precursor(s) comprise a **mixture of** ß-diketonate **[ligand]** **compound** selected from the group consisting of $La(thd)_3$, $Ca(thd)_2$ and $Mn(thd)_3$.

15. (amended) **[A]** **The** method according to claim 1**[4]**, wherein the precursor(s) comprise a mixture of ß-diketonate **[ligand]** **compounds** selected from the group consisting of $La(thd)_3$, $Sr(thd)_2$ and $Mn(thd)_3$.

16. (amended) **[A]** **The** method according to claim 14, wherein said precursor(s) comprise a mixture of Lewis base adducts of metal ß-diketonate precursors.

17. (amended) **[A]** **The** method according to claim 1, wherein said **[thin film]** manganate material has A-site deficient stoichiometry, where (La+Ca) < **[1.0]** **0.9**.

18. (amended) **[A]** **The** method according to claim 1, wherein said **[thin film]** manganate material has A-site deficient stoichiometry, where 0.5 < (La+Ca) < **[0.99]** **0.9**.

19. (amended) **[A]** **The** method according to claim 1, wherein said **[thin film]** manganate material has A-site deficient stoichiometry, where (La + Sr) < **[1.0]** **0.9.**

20. (amended) **[A]** **The** method according to claim 1, wherein said **[thin film]** manganate material has A-site deficient stoichiometry, where 0.5 < (La + Sr) < **[0.99]** **0.9**.

21. (amended) **[A]** **The** method according to claim 1, wherein said **[thin film]** manganate material has A-site deficient stoichiometry, where (La + Ba) < **[0.99]** **0.9.**

22. (amended) **[A]** **The** method according to claim 1, wherein said **[thin film]** manganate material has A-site deficient stoichiometry, where 0.5 < (La + Ba) < **[0.99]** **0.9**.

Please add the following new claim: